Low Skew, 1-to-6, Crystal/ LVCMOS/ Differential-to-3.3V, 2.5V LVPECL Fanout Buffer

DATA SHEET

GENERAL DESCRIPTION

The ICS8536-01 is a low skew, high performance 1-to-6 Selectable Crystal, Single-Ended, or Differential Input-to-3.3V, 2.5V LVPECL Fanout Buffer. The ICS8536-01 has selectable crystal, single ended or differential clock inputs. The single ended clock input accepts LVCMOS or LVTTL input levels and translates them to LVPECL levels. The CLK1, nCLK1 pair can accept most standard differential input levels. The output enable is internally synchronized to eliminate runt pulses on the outputs during asynchronous assertion/deassertion of the clock enable pin.

Guaranteed output and part-to-part skew characteristics make the ICS8536-01 ideal for those applications demanding well defined performance and repeatability.

FEATURES

- Six 3.3V, 2.5V LVPECL outputs
- Selectable crystal oscillator, differential CLK1, nCLK1 pair or LVCMOS/LVTTL clock input
- CLK1, nCLK pair can accept the f ollowing differential input levels: LVPECL, LVDS, LVHSTL, SSTL, HCSL
- Maximum output frequency: 700MHz
- Crystal frequency range: 12MHz 40MHz
- Output skew: 55ps (maximum) CLK1, nCLK1 @ 3.3V
- Part-to-part skew: 450ps (maximum)
- Additive phase jitter, RMS: 0.19ps (typical)
- Full 3.3V or 2.5V supply mode
- 0°C to 70°C ambient operating temperature
- Available in lead-free (RoHS 6) pac kages

BLOCK DIAGRAM



PIN ASSIGNMENT

nQ2 🗆	1	24	D Q3
Q2 🗖	2	23	🗆 nQ3
Vcc 🗖	3	22	UCC VCC
nQ1 🗖	4	21	🗆 Q4
Q1 🗖	5	20	⊐ nQ4
Vee 🗖	6	19	UCC VCC
nQ0 🗖	7	18	🗆 Q5
Q0 🗆	8	17	🗆 nQ5
CLK_SEL0	9	16	CLK_SEL1
XTAL_IN	10	15	nCLK1
XTAL_OUT	11	14	CLK1
CLK_EN	12	13	CLK0

ICS8536-01 24-Lead TSSOP 4.40mm x 7.8mm x 0.925mm package body G Package Top View

TABLE 1. PIN	DESCRIPTIONS
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Namber	Nem	Tj	мр	Descriptio
122	nQ2, Q	Outpu		Differential output pair. LVPECL interface levels
3,V19, 22	сс	Power		Power supply pins
4,15	nQ1, Q	Outpu		Differential output pair. LVPECL interface levels
6V	EE	Power		Negative supply pin
708	nQ0, Q	Oupu		Differential output pair. LVPECL interface levels
9, 16	CLK_SEL0, CLK_SEL1	Input	Pulldow	Clock select pins. LVCMOS/LVTTL interface levels. See Table 3B.
10, 11	XTAL_IN, XTAL_OUT	Input		Parallel resonant crystal interface. XTAL_OUT is the output, XTAL_IN is the input.
1図	CLK_E	Ip pu	Pullu	Synchronizing clock enable. When HIGH, clock outputs follow clock input. When LOW, the outputs are disabled. LVCMOS / LVTTL interface levels. See Table 3A.
10	CŁK	l n pu	Pulldow	LVCMOS/LVTTL clock input
14	CŁK	Inpu	Pulldow	Non-inverting differential clock input
15	nCLK	Ippu	Pullu	Inverting differential clock input
15, 18	nQ5, Q	Outpu		Differential output pair. LVPECL interface levels
20, 21	nQ4, Q	Outpu		Differential output pair. LVPECL interface levels
23, 24	nQ3, Q	Outpu		Differential output pair. LVPECL interface levels

NOTE: Pullup and Pulldown refer to internal input resistors. See Table 2, Pin Characteristics, for typical values.

TABLE 2. PIN CHARACTERISTICS

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			4		pF
R _{PULLDOWN}	Input Pulldown Resistor			51		kΩ
R _{PULLUP}	Input Pulup Resistor			51		kΩ

TABLE 3A. CONTROL INPUT FUNCTION TABLE

	I	Out	puts		
CLK_EN	CLK_SEL1	CLK_SEL0	Selected Source	Q0:Q5	nQ0:nQ5
0	0	0	XTAL	Disabled	Disabled
0	0	1	CLK0	Disabled	Disabled
0	1	Х	CLK1, nCLK1	Disabled	Disabled
1	0	0	XTAL	Enabled	Enabled
1	0	1	CLK0	Enabled	Enabled
1	1	Х	CLK1, nCLK1	Enabled	Enabled

After CLK_EN switches, the clock outputs are disabled or enabled following a rising and falling input clock edge as show in *Figure 1.*

In the active mode, the state of the outputs are a function of the selected clock input as described in Table 3B.



FIGURE 1. CLK_EN TIMING DIAGRAM

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V_{cc}	4.6V
Inputs, V _I	-0.5V to V_{cc} + 0.5V
Outputs, I _o Continuous Current Surge Current	50mA 100mA
Package Thermal Impedance, $\theta_{_{J\!A}}$	84.6°C/W (0 mps)
Storage Temperature, T _{STG}	-65°C to 150°C

NOTE: Stresses be yond those listed under Absolute Maximum Ratings may cause per manent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or an y conditions be yond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Table 4A. Power Supply DC Characteristics, $V_{cc} = 3.3V \pm 5\%$, $V_{ee} = 0V$, TA = 0°C to 70°C

Symbol	P a ramete	Test Condition	Minimu	Тупріса	Maximu	Unit
V _{cc}	Power Supply Voltage		33135	35	3.46	
I _{EE}	Power Supply Current				8 6	m

Table 4B. Power Supply DC Characteristics, V_{cc} = 2.5V±5%, TA = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{cc}	Power Supply Voltage		2.375	2.5	2.625	V
I _{EE}	Power Supply Current				85	mA

TABLE 4C. LVCMOS / LVTTL DC Characteristics, $V_{CC} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $V_{EE} = 0V$, TA = 0°C to 70°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V			V _{cc} =23.3V			V _{cc} + 0.3	V
V _{IH}	input nigh voi	lage	V _{cc} =72.5V	1./		_{cc} +\0.3	
V	Input Low Voltage		V _{cc} =33.3V	- θ.		0.V	
VIL		laye	V _{cc} =32.5V	-Ø.		0.V	
	Input High Current	CLK0, CLK_SEL0:1	$V_{\rm CC} = V_{\rm IN} = 08.465 \text{V or } 2.625 \text{V}$			1£3	μ
		C I ∕K_EN	$_{\rm CC}$ = V _{IN} =53.465V or 2.625V				μA
	Input	CLK0, CLK_SEL0:1	$V_{cc} = 3.465V \text{ or } 2.625V, V_{IN} = 50V$	-A			μ
	Low Current	C ∕K_EN	$_{\rm cc}$ = 3.465V or 2.625V, V $_{\rm IN}$ =00V	-A 5			μ

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
	Input High Current	nCLK1	$V_{cc} = V_{IN} = 3.465V \text{ or } 2.625V$			5	μA
'н	Input High Current	CLK1	$V_{\rm CC} = V_{\rm IN} = 3.465 V$			150	μA
		nữLK1	$_{\rm CC}$ = 3.465V or 2.625V, V $_{\rm IN}$ =00V	- #5			μ
Input	Input Low Current	C I∕K1	$_{\rm CC}$ = 3.465V or 2.625V, V $_{\rm IN}$ =50V	-A			μ
V _{PP}	Peak-to-Peak Input Voltage; NOTE 1			0315		1.V	
V _{CMR}	Common Mode Inpl NOTE 1, 2	ut Voltage;		V _{EE} +\Ø.5		_{cc} -\0.85	

TABLE 4D. DIFFERENTIAL DC CHARACTERISTICS, $V_{CC} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $V_{ee} = 0V$, TA = 0°C to 70°C

NOTE 1: V_{IL} should not be less than -0.3V. NOTE 2: Common mode voltage is defined as V_{IH} .

TABLE 4E. LVPECL DC CHARACTERISTICS, $V_{CC} = 3.3V \pm 5\%$, $V_{EE} = 0V$, TA = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{OH}	Output High Voltage; NOTE 1		V _{cc} - 1.4		V _{cc} - 0.9	V
V _{ol}	Output Low Voltage; NOTE 1		V _{cc} - 2.0		V _{cc} - 1.7	V
V _{SWING}	Peak-to-Peak Output Voltage Swing		0.6		1.0	V

NOTE 1: Outputs terminated with 50 Ω to V $_{cc}$ - 2V.

TABLE 4F. LVPECL DC Characteristics, $V_{cc} = 2.5V \pm 5\%$, $V_{ee} = 0V$, TA = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{OH}	Output High Voltage; NOTE 1		V _{cc} - 1.4		V _{cc} - 0.9	V
V _{ol}	Output Low Voltage; NOTE 1		V _{cc} - 2.0		V _{cc} - 1.5	V
V _{SWING}	Peak-to-Peak Output Voltage Swing		0.4		1.0	V

NOTE 1: Outputs terminated with 50 Ω to V $_{cc}$ - 2V.

TABLE 5. CRYSTAL CHARACTERISTICS

Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation		Fι	Indamenta	al	
Frequency		10		4z	MH
Equivalent Series Resistance (ESR)				50	Ω
Shunt Capacitance				7F	р
Drive Level				1W	m

NOTE: Characterized using an 18pF parallel resonant crystal.

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
4		CLK1/nCLK1				700	MHz
OUT	Output Frequency	CLK0				300	MHz
	Propagation Delay,	CLK1/nCLK1		1.7		2.5	ns
ч _{РD}	NOTE1A, 1B	CLK0		1.35		2.0	ns
<i>t</i> jit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 2		CLK1/nCLK1, 155.52MHz, Integration Range: 12kHz - 20MHz		0.19		ps
<i>t</i> sk(o)	Output Skew; NOTE 3, 5					55	ps
<i>t</i> sk(pp)	Part-to-Part Skew; NOTE 4, 5					450	ps
t _R / t _F	Output Rise/Fall Tin	ne	20% to 80%	200		700	ps
ada	Output Duty Cycle	CLK1/nCLK1		48		52	%
ouc		CLK0		44		56	%
MUX_ISOLATION		NOTE 6A	<i>f</i> = 150MHz		-76		dB
	NOTE 6B		f = 250MHz		-75		dB

TABLE 6A. AC CHARACTERISTICS, $V_{CC} = 3.3V \pm 5\%$, $V_{EE} = 0V$, TA = 0°C to 70°C

All parameters measured at $f_{OUT} \le 300 MHz$ unless noted otherwise.

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

The cycle-to-cycle jitter on the input will equal the jitter on the output. The part does not add jitter

NOTE 1A: Measured from the differential input crossing point to the differential output crossing point.

NOTE 1B: Measured from $V_{cc}/2$ input crossing point to the differential output crossing point.

NOTE 2: Driving only one input clock.

NOTE 3: Defined as skew between outputs at the same supply voltage and with equal load conditions.

Measured at the output differential cross points.

NOTE 4: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross points.

NOTE 5: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 6A: CLK0 (150MHz) sensitivity is measured with CLK_SEL[1:0] = 00.

NOTE 6B: CLK0 (250MHz) sensitivity is measured with CLK_SEL[1:0] = 1X.

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
£		CLK1, nCLK1				700	MHz
MAX	Output Frequency	CLK0				300	MHz
+	Propagation Delay,	CLK1, nCLK1		1.7		2.65	ns
ι _{PD}	NOTE1A, 1B	CLK0		1.4		2.05	ns
<i>t</i> jit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 2		CLK1, nCLK1, 155.52MHz, Integration Range: 12kHz - 20MHz		0.19		ps
<i>t</i> sk(o)	Output Skew; NOTE 3, 5					55	ps
<i>t</i> sk(pp)	Part-to-Part Skew; NOTE 4, 5					450	ps
t _R / t _F	Output Rise/Fall Tim	ne	20% to 80%	200		700	ps
ode	Output Duty Cycle	CLK1, nCLK1		48		52	%
UUC		CLK0		46		54	%
MUX_ISOLATION		NOTE 6A	<i>f</i> = 150MHz		-76		dB
		NOTE 6B	<i>f</i> = 250MHz		-75		dB

TABLE 6B. AC CHARACTERISTICS, $V_{CC} = 2.5V \pm 5\%$, $V_{EE} = 0V$, TA = 0°C to 70°C

For notes, see Table 6A above.

Additive Phase Jitter

The spectral pur ity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the *dBc Phase Noise*. This value is normally expressed using a Phase noise plot and is most often the specified plot in man y applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the po wer value of the fundamental. This ratio is expressed in decibels (dBm) or a r atio of the po wer in the 1Hz

band to the power in the fundamental. When the required offset is specified, the phase noise is called a *dBc* value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, w e get a better understanding of its eff ects on the desired application o ver the entire time record of the signal. It is mathematically possib le to calculate an expected bit error r ate given a phase noise plot.



OFFSET FROM CARRIER FREQUENCY (Hz)

As with most timing specifications , phase noise measurements have issues relating to the limitations of the measurement equipment. The noise floor of the equipment can be higher or lower than the noise floor of the de vice. Additive phase noise is dependent on both the noise floor of the input source and measurement equipment.

PARAMETER MEASUREMENT INFORMATION





APPLICATION INFORMATION

WIRING THE DIFFERENTIAL INPUT TO ACCEPT SINGLE ENDED LEVELS

Figure 2 shows how a diff erential input can be wired to accept single ended levels. The reference voltage $V_1 = V_{cc}/2$ is generated by the bias resistors R1 and R2. The bypass capacitor (C1) is used to help filter noise on the DC bias This bias circuit should be located as close to the input pin as possib le. The ratio of R1 and R2 might need to be adjusted to position the V_{REF} in the center of the input v oltage swing. For example, if the input cloc k swing is 2.5V and $V_{cc} = 3.3V$, R1 and R2 value should be adjusted to set V_1 at 1.25V. The values below are f or when both the single-ended swing and V_{cc} are at the same voltage. This configuration requires that the sum of the output impedance of the dr iver (Ro) and the series resistance (Rs) equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in one of tw o ways. First, R3 and R4 in parallel should equal the transmission line impedance. For most

50 applications, R3 and R4 can be 1000. The values of the resistors can be increased to reduce the loading f or slo wer and w eaker LVCMOS dr iver. When using single ended signaling, the noise rejection benefits of differential signaling are reduced. Even though the differential input can handle full r ail LVCMOS signaling, it is recommended that the amplitude be reduced. The datasheet specifies a lower differential amplitude, however this only applies to differential signals. For single-ended applications, the swing can be larger, however $V_{_{\rm IL}}$ cannot be less than -0.3V and $V_{_{\rm IH}}$ cannot be more than $V_{cc} + 0.3V$. Though some of the recommended components might not be used, the pads should be placed in the layout. They can be utilized for debugging purposes. The datasheet specifications are char acterized and guar anteed by using a differential signal.



FIGURE 2. SINGLE ENDED SIGNAL DRIVING DIFFERENTIAL INPUT

CRYSTAL INPUT INTERFACE

The ICS8536-01 has been char acter ized with 18pF par allel resonant crystals. The capacitor values shown in *Figure 2* below were deter mined using an 18pF parallel resonant crystal and were chosen to minimize the ppm error.



FIGURE 2. CRYSTAL INPUT INTERFACE

OVERDRIVING THE CRYSTAL INTERFACE

The XTAL_IN input can be overdriven by an LVCMOS driver or by one side of a differential driver through an AC coupling capacitor. The XTAL_OUT pin can be left floating. The amplitude of the input signal should be betw een 500mV and 1.8V and the slew rate should not be less than 2V/nS. For 3.3V LVCMOS inputs, the amplitude must be reduced from full s wing to at least half the swing in order to prevent signal interference with the power rail and to reduce internal noise. *Figure 3* shows an example of the interface diagram for a high speed 3.3V LVCMOS driver. This configuration requires that the sum of the output impedance of the driver (Ro) and the series resistance (Rs) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the

signal in half. This can be done in one of tw o ways. First, R1 and R2 in parallel should equal the transmission line impedance. For most 50 Ω applications, R1 and R2 can be 100 Ω . This can also be accomplished by removing R1 and changing R2 to 50 Ω . The values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver. Figure 3 shows an example of the interface diagram for an LVPECL driver. This is a standard LVPECL termination with one side of the dr iver feeding the XTAL_IN input. It is recommended that all components in the schematics be placed in the la yout. Though some components might not be used, the y can be utilized for debugging purposes. The datasheet specifications are char acterized and guaranteed by using a quartz crystal as the input.



FIGURE 3A. GENERAL DIAGRAM FOR LVCMOS DRIVER TO XTAL INPUT INTERFACE



FIGURE 3B. GENERAL DIAGRAM FOR LVPECL DRIVER TO XTAL INPUT INTERFACE

DIFFERENTIAL CLOCK INPUT INTERFACE

The CLK, nCLK accepts LVDS, LVPECL, LVHSTL, SSTL, HCSL and other differential signals. Both V_{SWING} and V_{OH} must meet the V_{PP} and V_{CMR} input requirements . *Figures 4A to 4F* show interface examples for the CLK, nCLK input dr iven by the most common diver types. The input interfaces suggested here are examples only. Please consult with the vendor of the



FIGURE 4A. CLK, NCLK INPUT DRIVEN BY AN IDT OPEN EMITTER LVHSTL DRIVER



FIGURE 4C. CLK, NCLK INPUT DRIVEN BY A 3.3V LVPECL DRIVER



FIGURE 4E. CLK, NCLK INPUT DRIVEN BY A 3.3V HCSL DRIVER

driver component to confir m the dr iver ter mination requirements. For example in Figure 4A, the input termination applies for IDT open emitter LVHSTL drivers. If you are using an LVHSTL driver from another vendor, use their termination recommendation.



FIGURE 4B. CLK, NCLK INPUT DRIVEN BY A 3.3V LVPECL DRIVER



FIGURE 4D. CLK, NCLK INPUT DRIVEN BY A 3.3V LVDS DRIVER



FIGURE 4F. CLK, NCLK INPUT DRIVEN BY A 2.5V SSTL DRIVER

RECOMMENDATIONS FOR UNUSED INPUT AND OUTPUT PINS

NPUTS:

CRYSTAL INPUTS

For applications not requiring the use of the crystal oscillator input, both XTAL_IN and XT AL_OUT can be left floating. Though not required, but for additional protection, a 1k Ω resistor can be tied from XTAL_IN to g round.

CLK INPUT

For applications not requir ing the use of the cloc k, it can be left floating. Though not required, b ut for additional protection, a 1k Ω resistor can be tied from the CLK input to g round.

CLK/nCLK INPUTS

For applications not requir ing the use of the diff erential input, both CLK and nCLK can be left floating. Though not required, but for additional protection, a 1k Ω resistor can be tied from CLK to ground.

LVCMOS CONTROL PINS

All control pins have internal pull-ups or pull-downs; additional resistance is not required but can be added for additional protection. A $1k\Omega$ resistor can be used.

TERMINATION FOR 3.3V LVPECL OUTPUTS

The clock layout topology shown below is a typical termination for LVPECL outputs. The two different layouts mentioned are recommended only as guidelines.

The differential outputs are low impedance follower outputs that generate ECL/LVPECL compatible outputs. Therefore, ter minating resistors (DC current path to ground) or current sources must be used f or functionality. These outputs are designed to



FIGURE 5A. LVPECL OUTPUT TERMINATION

OUTPUTS:

LVPECL OUTPUTS

All unused LVPECL outputs can be left floating. We recommend that there is no tace attached. Both sides of the differential output pair should either be left floating or ter minated.

drive 50Ω transmission lines. Matched impedance techniques should be used to maximize operating frequency and minimize signal distortion. *Figures 5A and 5B* show two different layouts which are recommended only as guidelines . Other suitab le clock layouts may exist and it would be recommended that the board designers simulate to guarantee compatibility across all printed circuit and clock component process variations.



FIGURE 5B. LVPECL OUTPUT TERMINATION

TERMINATION FOR 2.5V LVPECL OUTPUTS

Figure 6A and *Figure 6B* show examples of termination for 2.5V LVPECL driver. These terminations are equivalent to terminating 50 Ω to V_{cc} - 2V. For V_{cc} = 2.5V, the V_{cc} - 2V is very close to ground



FIGURE 6A. 2.5V LVPECL DRIVER TERMINATION EXAMPLE



FIGURE 6C. 2.5V LVPECL TERMINATION EXAMPLE

level. The R3 in Figure 6B can be eliminated and the ter mination is shown in *Figure 6C*.



FIGURE 6B. 2.5V LVPECL DRIVER TERMINATION EXAMPLE

POWER CONSIDERATIONS

This section provides information on power dissipation and junction temper ature for the ICS8536-01. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the ICS8536-01 is the sum of the core po wer plus the power dissipated in the load(s). The following is the power dissipation for $V_{cc} = 3.3V + 5\% = 3.465V$, which gives worst case results. **NOTE:** Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)_{MAX} = V_{CC MAX} * I_{EE MAX} = 3.465V * 85mA = 294.525 mW
- Power (outputs)_{MAX} = 30mW/Loaded Output pair
 If all outputs are loaded, the total po wer is 6 * 30mW = 180mW

Total Power $_{Max}$ (3.465V, with all outputs switching) = 294.525mW + 180mW = 474.525mW

2. Junction Temperature.

Junction temperature at the junction of the bond wire and bond pad directly aff ects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, Tj, to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for Tj is as follows: $Tj = \theta_{JA} * Pd_total + T_A$

Tj = Junction Temperature

 $\theta_{JA} = J$ unction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temper ature, the appropriate junction-to-ambient ther mal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 84.6°C/W per Table 7 below.

Therefore, Tj for an ambient temper ature of 70°C with all outputs s witching is: $70^{\circ}C + 0.475W * 84.6^{\circ}C/W = 110.2^{\circ}C$. This is below the limit of $125^{\circ}C$.

This calculation is only an e xample. Tj will obviously vary depending on the n umber of loaded outputs, supply voltage, air flow, and the type of board (single la yer or multi-layer).

TABLE 7. THERMAL RESISTANCE θ_{JA} FOR 24-PIN TSSOP, FORCED CONVECTION

θ _{JA} by Velocity (Meters per Second)						
	Multi-Layer PCB, JEDEC Standard Test Boards	0 84.6°C/W	1 80.3°C/W	2.5 78.1°C/W		

3. Calculations and Equations.

The purpose of this section is to der ive the power dissipated into the load.

LVPECL output driver circuit and termination are shown in Figure 7.



FIGURE 7. LVPECL DRIVER CIRCUIT AND TERMINATION

To calculate power dissipation due to the load, use the f ollowing equations which assume a 50 Ω load, and a termination voltage of V $_{cc}$ - 2V.

• For logic high, $V_{out} = V_{OH_{MAX}} = V_{CC_{MAX}} - 0.9V$

$$(V_{CC_{MAX}} - V_{OH_{MAX}}) = 0.9V$$

• For logic low, $V_{OUT} = V_{OL_MAX} = V_{CC_MAX} - 1.7V$ $(V_{CC_MAX} - V_{OL_MAX}) = 1.7V$

Pd_H is power dissipation when the output dr ives high. Pd_L is the power dissipation when the output dr ives low.

 $\begin{aligned} \mathsf{Pd}_{-}\mathsf{H} &= [(\mathsf{V}_{_{\mathsf{OH}_MAX}} - (\mathsf{V}_{_{\mathsf{CC}_MAX}} - 2\mathsf{V}))/\mathsf{R}_{_}] * (\mathsf{V}_{_{\mathsf{CC}_MAX}} - \mathsf{V}_{_{\mathsf{OH}_MAX}}) = [(2\mathsf{V} - (\mathsf{V}_{_{_{\mathsf{CC}_MAX}}} - \mathsf{V}_{_{\mathsf{OH}_MAX}}))/\mathsf{R}_{_}] * (\mathsf{V}_{_{_{\mathsf{CC}_MAX}}} - \mathsf{V}_{_{\mathsf{OH}_MAX}}) = [(2\mathsf{V} - 0.9\mathsf{V})/50\ \Omega] * 0.9\mathsf{V} = \mathbf{19.8}\mathsf{mW}\end{aligned}$

 $Pd_{L} = [(V_{ol_{MAX}} - (V_{cc_{MAX}} - 2V))/R_{L}] * (V_{cc_{MAX}} - V_{ol_{MAX}}) = [(2V - (V_{cc_{MAX}} - V_{ol_{MAX}}))/R_{L}] * (V_{cc_{MAX}} - V_{ol_{MAX}}) = [(2V - 1.7V)/50 \Omega] * 1.7V = 10.2mW$

Total Power Dissipation per output pair = Pd_H + Pd_L = **30mW**

Reliability Information

TABLE 8. θ_{JA} vs. Air Flow Table for 24 Lead TSSOP

θ _{JA} by Velocity (Meters per Second)					
Multi-Layer PCB, JEDEC Standard Test Boards	0 84.6°C/W	1 80.3°C/W	2.5 78.1°C/W		

TRANSISTOR COUNT

The transistor count for ICS8536-01 is: 513

PACKAGE OUTLINE - G SUFFIX FOR 24 LEAD TSSOP



TABLE 9. PACKAGE DIMENSIONS

SYMPOL	Millin	neters	
STMBOL	Minimum	Maximu	
N4	2		
A-	-0	1.2	
A 5	050	0.1	
AØ	058	1.0	
b9	001	0.3	
c9	000	0.2	
D0	707	7.9	
EC	6.40 BASI		
E0 403		4.5	
eC	0.65 BASI		
L5	054	0.7	
α	0°	8	
aaa	-0	0.1	

Reference Document: JEDEC Publication 95, MO-153

TABLE 10. ORDERING INFORMATION

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
ICS8536AG-01LF	ICS8536AG-01L	24 Lead "Lead-Free" TSSOP	tube	0°C to 70°C
ICS8536AG-01LFT	ICS8536AG-01L	24 Lead "Lead-Free" TSSOP	tape & reel	0°C to 70°C

Revision History Sheet

Rev	Table	Page	Description of Changes	Date
			Removed HiPerClock references throughout.	
			Updated diagrams to current standard throughout.	
		1	Features List: Removed non lead-free package.	
	4A, 4B	4	Vcc: changed Core Supply Voltage to Power Supply Voltage.	
	6A	6	Per PCN #Table Note: changed f_{MAX} to $f_{OUT} \leq 300$ MHz.	0/47/40
В	6B	6	t _{en} : 2.0ns (Max) to 2.6ns (Max).	8/17/12
		15, 16	Updated text in Power Considerations section.	
	10	19	Removed non lead-free ordering options and note. Removed quantity from T&R.	
			Deleted disclaimer at bottom of page 19.	
		20	Updated disclaimer on last page.	



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